

COMPLEMENTARY SILICON POWER TRANSISTORS

DESCRIPTION :

- Excellent Safe Operating Area
- High DC Current Gain-hFE=15(Min)@I_C = -8A
- Low Saturation Voltage-
: V_{CE(SAT)}= -1.4V(Max)@ I_C = -8A
- Complement to Type 2N3773

APPLICATIONS :

- Designed for high power audio ,disk head positioners and other linear applications, which can also be used in power switching circuits such as relay or solenoid drivers, DC-DC converters or inverters.

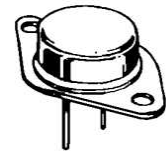
PNP

2N6609H

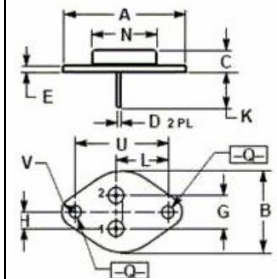
**16 AMPERES
COMPLEMENTARY
SILICON
POWER TRANSISTOR
140 VOLTS
150 WATTS**

MAXIMUM RATINGS

Rating	Symbol	2N6609H	Unit
Collector-Emitter Voltage	V _{CEO}	-140	V
Collector-Emitter Voltage	V _{CEX}	-160	V
Collector-Base Voltage	V _{CB0}	160	V
Emitter-Base Voltage	V _{EBO}	-7	V
Collector Current-Continuous	I _C	-16	A
Collector Current-Peak	I _{CP}	-30	A
Base Current-Continuous	I _B	-4	A
Total Power Dissipation @TC=25°C	P _D	150	Watts
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-65 to +150	°C



TO-3



PIN 1.BASE.
2.EMITTER
COLLECTOR(CASE)

DIM	MILLIMETERS	
	MIN	MAX
A	39.00	
B	25.3	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
O	4.00	4.20
U	30.00	30.20
V	4.30	4.50

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R _{th j-c}	1.17	°C/W

ELECTRICAL CHARACTERISTICS ($T_c=25^{\circ}\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min.	Max	Unit
----------------	--------	------	-----	------

OFF CHARACTERISTICS

Collector-Emitter Sustaining Voltage ($I_C = 50 \text{ mA}$, $I_B = 0$)	$V_{CE(SUS)}$	-140		V
Collector Cutoff Current ($V_{CE} = -120 \text{ V}$, $I_B = 0$)	I_{CEO}		-10	mA
Emitter Cutoff Current ($V_{EB} = -7.0 \text{ V}$, $I_C = 0$)	I_{EBO}		-5	mA

ON CHARACTERISTICS(1)

DC Current Gain ($I_C = -8 \text{ A}$, $V_{CE} = -4 \text{ V}$) ($I_C = -16 \text{ A}$, $V_{CE} = -4 \text{ V}$)	h_{FE}	15 5	85	
Collector-Emitter Saturation Voltage ($I_C = -8 \text{ A}$, $I_B = -0.8 \text{ A}$) ($I_C = -16 \text{ A}$, $I_B = -3.2 \text{ A}$)	$V_{CE(SAT)}$		-1.4 -4.0	V
Base-Emitter On Voltage ($I_C = -8 \text{ A}$, $V_{CE} = -4 \text{ V}$)	$V_{BE(ON)}$		-2.2	V

Notice

MOSPEC reserves the rights to make changes of the content herein the document anytime without notification. MOSPEC or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies. Please refer to MOSPEC website for the last document.

MOSPEC disclaims any and all liability arising out of the application or use of any product including damages incidentally and consequentially incurred.

Application shown on the herein document are examples of standard use and operation. Customers are responsible for comprehending suitable use in particular applications. MOSPEC makes no representation or warranty that such application will be suitable for the specified use without further testing or modification.

The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by MOSPEC for any infringements of patents or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of MOSPEC or others.

These MOSPEC products are intended for usage in general electronic equipment. Please make sure to consult with MOSPEC before you use these MOSPEC products in equipment which require specialized quality and/or reliability, and in equipment which could have major impact to the welfare of human life (atomic energy control, aeronautics , traffic control, combustion control, safety devices etc.)